

L Number	Hits	Search Text	DB	Time stamp
1	4335	(372/29.021,45,46,50).CCLS.	USPAT; US-PGPUB	2004/02/19 15:26
2	648	((372/29.021,45,46,50).CCLS.) and aperture	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/19 15:29
4	2751	((372/29.021,45,46,50).CCLS.) and mode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/19 15:27
3	13	((((372/29.021,45,46,50).CCLS.) and aperture) and protrusion	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/19 15:27
5	7	((372/29.021,45,46,50).CCLS.) and (hole opening aperture) with (protrusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/19 15:29
6	17	((372/29.021,45,46,50).CCLS.) and (hole opening aperture) with (protru\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/19 15:29
-	512	(semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))	USPAT; EPO; JPO; DERWENT	2002/03/27 10:16
-	45	((semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))) and ("near" near2 field)	USPAT; EPO; JPO; DERWENT	2002/03/26 18:47
-	146	((semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))) and (mesa protrusion ridge)	USPAT; EPO; JPO; DERWENT	2002/03/26 18:48
-	115	((((semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))) and (mesa protrusion ridge)) not (((semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))) and ("near" near2 field)))	USPAT; EPO; JPO; DERWENT	2002/03/26 19:27
-	9288	xerox.as. and laser	USPAT; EPO; JPO; DERWENT	2002/03/26 20:03
-	1666	(xerox.as. and laser) and (semiconductor with laser)	USPAT; EPO; JPO; DERWENT	2002/03/26 20:04
-	176	((xerox.as. and laser) and (semiconductor with laser)) and aperture	USPAT; EPO; JPO; DERWENT	2002/03/26 20:04
-	17	((((xerox.as. and laser) and (semiconductor with laser)) and aperture) and ((xerox.as. and laser) and (thornton chua treat shi).in.)	USPAT; EPO; JPO; DERWENT	2002/03/26 20:13
-	171	(xerox.as. and laser) and (thornton chua treat shi).in.	USPAT; EPO; JPO; DERWENT	2002/03/26 20:05
-	159	((((xerox.as. and laser) and (semiconductor with laser)) and aperture) not ((xerox.as. and laser) and (thornton chua treat shi).in.)	USPAT; EPO; JPO; DERWENT	2002/03/26 20:14
-	2	6317447.pn.	USPAT; EPO; JPO; DERWENT	2002/03/27 09:02
-	2	5903589.pn. and aperture	USPAT; EPO; JPO; DERWENT	2002/03/27 10:27
-	5	((("6304588") or ("6297068") or ("6208681") or ("5978408"))).PN.	USPAT; EPO; JPO; DERWENT	2002/03/27 13:44

-	17	("5331654" "5412680" "5493577" "5727014" "5896408" "6075804" "6208681").PN.	USPAT; EPO; JPO; DERWENT	2002/03/27 14:00
-	16	("5359618" "5373522" "5493577" "5719891" "5719892" "5896408").PN.	USPAT; EPO; JPO; DERWENT	2002/03/27 13:52
-	5	("5493577" "5978408").PN.	USPAT; EPO; JPO; DERWENT	2002/03/27 13:55
-	42	("4216036" "5115441" "5262360" "5327448" "5337074" "5359618" "5373522" "5403775" "5493577" "5550081" "5719891" "5719892" "5724374" "5729566" "5896408").PN.	USPAT; EPO; JPO; DERWENT	2002/04/05 18:32
-	4338	(372/29.021,45,50).CCLS.	USPAT; EPO; JPO; DERWENT	2002/03/27 14:00
-	3460	((372/29.021,45,50).CCLS.) and (semiconductor near3 laser)	USPAT; EPO; JPO; DERWENT	2002/03/27 14:01
-	1503	((((372/29.021,45,50).CCLS.) and (semiconductor near3 laser)) and (aperture hole opening recess)	USPAT; EPO; JPO; DERWENT	2002/03/27 14:02
-	1532	((((372/29.021,45,50).CCLS.) and (semiconductor near3 laser)) and (aperture hole opening recess protrusion)	USPAT; EPO; JPO; DERWENT	2002/03/27 14:03
-	1510	(((((372/29.021,45,50).CCLS.) and (semiconductor near3 laser)) and (aperture hole opening recess protrusion)) and (@ad<19990830)	USPAT; EPO; JPO; DERWENT	2002/03/27 14:04
-	2	("6078599").PN.	USPAT; EPO; JPO; DERWENT	2002/03/27 15:39
-	7193	(semiconductor near3 laser) and (aperture opening hole) and (mirror reflector)	USPAT; EPO; JPO; DERWENT	2002/04/05 18:36
-	6834	((semiconductor near3 laser) and (aperture opening hole) and (mirror reflector)) and (@ad<19990830)	USPAT; EPO; JPO; DERWENT	2002/04/05 18:37
-	1601	((((semiconductor near3 laser) and (aperture opening hole) and (mirror reflector)) and (@ad<19990830)) and 372/\$.ccls.	USPAT; EPO; JPO; DERWENT	2002/04/05 18:38
-	160	(((((semiconductor near3 laser) and (aperture opening hole) and (mirror reflector)) and (@ad<19990830)) and 372/\$.ccls.) and VCSEL	USPAT; EPO; JPO; DERWENT	2002/04/05 18:39
-	15	("4216036" "5115441" "5262360" "5327448" "5337074" "5359618" "5373522" "5403775" "5493577" "5550081" "5719891" "5719892" "5724374" "5729566" "5896408").PN.	USPAT	2002/04/05 18:56
-	3695	laser and (resonator cavity) and energy and (relax\$5 (build adj up))	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:15
-	2992	(laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:22
-	1574	((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:18
-	176	((((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))) and steady near2 state	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:18
-	135	((((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))) and pulse with interval	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:19
-	395	(((((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))) and (periodic non-periodic)	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:19

-	12	((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))) and (periodic non-periodic) with interrupt\$5	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:20
-	137	((laser and (resonator cavity) and energy and (relax\$5 (build adj up))) and (relaxation (build adj up))) and (crystal (non adj2 linear))) and phase near2 match\$3	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:20
-	2222	(372/25,26,30,38.06,70-72,75).CCLS.	USPAT	2002/07/08 15:21
-	1044	((372/25,26,30,38.06,70-72,75).CCLS.) and (cavity resonator) and energy	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:21
-	252	((372/25,26,30,38.06,70-72,75).CCLS.) and harmonic and crystal	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:22
-	357	((372/25,26,30,38.06,70-72,75).CCLS.) and (relaxation (build adj up))	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:22
-	138	((372/25,26,30,38.06,70-72,75).CCLS.) and steady near2 state	USPAT; EPO; JPO; IBM_TDB	2002/07/08 15:22
-	3	5247534.pn.	USPAT; EPO; JPO; DERWENT	2002/07/09 16:42
-	627	372/43-50.ccls. and aperture	USPAT; EPO; JPO; DERWENT	2003/08/20 13:56
-	6	(372/43-50.ccls. and aperture) and aperture with (protru\$5)	USPAT; EPO; JPO; DERWENT	2003/08/20 13:40
-	20	372/\$.ccls. and aperture with (protru\$5)	USPAT; EPO; JPO; DERWENT	2003/08/20 13:55
-	14	(372/\$.ccls. and aperture with (protru\$5)) not ((372/43-50.ccls. and aperture) and aperture with (protru\$5))	USPAT; EPO; JPO; DERWENT	2003/08/20 13:41
-	34	372/\$.ccls. and aperture with slot	USPAT; EPO; JPO; DERWENT	2003/08/20 13:55
-	4	372/43-50.ccls. and aperture with slot	USPAT; EPO; JPO; DERWENT	2003/08/20 13:56
-	39	372/43-50.ccls. and aperture with ((metal conduct\$4) near2 layer)	USPAT; EPO; JPO; IBM_TDB	2003/08/20 18:42
-	0	6529541.URPN.	USPAT	2003/08/20 18:37
-	3	("5245622" "5753941" "5838715").PN.	USPAT	2003/08/20 18:37
-	6	5753941.URPN.	USPAT	2003/08/20 18:40
-	1	"5633527".PN.	USPAT	2003/08/20 18:41
-	128	372/43-50.ccls. and aperture.ab.	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:12
-	41	(372/43-50.ccls. and aperture.ab.) and aperture with mode	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:07
-	21	(372/43-50.ccls. and aperture.ab.) and aperture with shape	USPAT; EPO; JPO; IBM_TDB	2003/08/20 18:54
-	1	(372/43-50.ccls. and aperture.ab.) and aperture with shape with mode	USPAT; EPO; JPO; IBM_TDB	2003/08/20 18:55
-	27	372/\$.ccls. and aperture with shape with mode	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:07

-	11	((372/43-50.ccls. and aperture.ab.) and aperture with mode) and (oxid\$6 with layer)	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:12
-	37	372/43-50.ccls. and aperture and DBR same oxide	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:13
-	36	(372/43-50.ccls. and aperture and DBR same oxide) and contact with layer	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:14
-	34	((372/43-50.ccls. and aperture and DBR same oxide) and contact with layer) and oxide with layer	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:18
-	0	(372/43-50.ccls. and vcsel and contact near3 layer and oxide near3 layer) and aperture	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:19
-	59	372/43-50.ccls. and vcsel and contact near3 layer and oxide near3 layer	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:33
-	5	("5115441" "5805624" "5879961" "5963576" "6021146").PN.	USPAT	2003/08/20 20:29
-	13	xerox.as. and vcsel and ITO	USPAT; EPO; JPO; IBM_TDB	2003/08/20 20:33
-	25	xerox.as. and sun.in. and vcsel	USPAT; EPO; JPO; DERWENT	2003/08/21 13:12